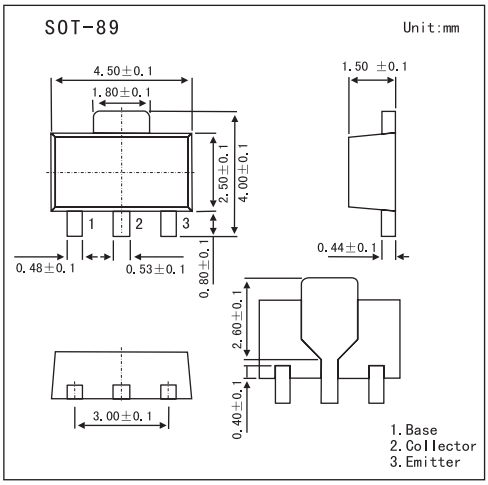
PNP Silicon Epitaxial Transistor

2SB1628



Features

- High current capacitance.
- Low collector saturation voltage.

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-20	V
Collector to Emitter Voltage	V_{CEO}	-16	V
Emitter to Base Voltage	V_{EBO}	-6	V
Collector Current (DC)	$I_{C(DC)}$	-3	A
Collector Current (pulse) *	$I_{C(Pulse)}$	-5	A
Base Current (DC)	$I_{B(DC)}$	-0.2	A
Base Current (pulse) *	$I_{B(Pulse)}$	-0.4	A
Total Power Dissipation	P_T	2	W
Junction Temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

* PW ⩽ 10 ms, Duty Cycle ⩽ 50%

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■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector Cut-off Current	I_{CBO}	V_{CBO} = -20 V, I_E = 0			-100	nA
Emitter Cut-off Current	I_{EBO}	V_{EBO} = -6.0 V, I_C = 0			-100	nA
DC Current Gain *	h_{FE1}	V_{CE} = -2.0 V, I_C = -0.5 A	140	280	560	
	h_{FE2}	V_{CE} = -2.0 V, I_C = -3.0 A	70			
Base to Emitter Voltage *	V_{BE}	V_{CE} = -2.0 V, I_C = -0.05 A	-600	-660	-700	mV
Collector Saturation Voltage *	$V_{CE(sat)1}$	I_C = -2.0 A, I_B = -0.1 A		-240	-350	mV
Collector Saturation Voltage *	$V_{CE(sat)2}$	I_C = -3.0 A, I_B = -0.15 A		-350	-550	mV
Base Saturation Voltage *	$V_{BE(sat)}$	I_C = -2.0 A, I_B = -0.1 A		-0.95	-1.2	V
Gain Bandwidth Product	f_T	V_{CE} = □3.0 V, I_E = 0.5 A		320		MHz
Output Capacitance	C_{ob}	V_{CB} = □10 V, I_E = 0, f = 1 MHz		45		pF
Turn-on Time	t_{on}	I_C = -1.0 A, V_{CC} = -10 V, R_L = 5.0 ？, I_{B1} = -I_{B2} = -0.1 A,		70		ns
Storage Time	t_{stg}			110		ns
Fall Time	t_f			40		ns

* Pulsed: PW ⩽ 350 μs, Duty Cycle ⩽ 2%.

■ h_{FE} Classification

Marking	ZX	ZY	ZZ
h_{FE}	140～280	200～400	280～560